

TDS1411P Transient Diverting Supressor 1-Line, 14V SurgeSwitch™ EOS Protection

PROTECTION PRODUCTS

Description

Semtech SurgeSwitch[™] Transient Diverting Suppressors (TDS) are designed to provide protection from Electrical Overstress (EOS) events. They have superior clamping and temperature characteristics when compared to standard TVS devices. The device uses a surge rated FET as the main protection element. A precisely tuned trigger circuit activates the shunt FET when an EOS event is detected. The TDS clamping voltage is nearly constant across the rated peak pulse current range due to the extremely low ON Resistance of the FET.

TDS1411P is designed to protect voltage bus or data lines with an operating voltage as high as 14V. It is rated for a high-energy transient current up to $40A(t_p = 8/20\mu s)$ and may be used to meet the common industrial voltage surge standard of $\pm 2kV$ ($R_s = 42\Omega$, $C_s = 0.5\mu F$).

TDS1411P is in a small DFN 1.6mm x 1.6mm x 0.55mm 6-Lead package and represents significant board space savings over traditional solutions.

Package Dimension (mm)



Features

- High ESD Withstand Voltage: ±30kV (Contact & Air) per IEC 61000-4-2
- High peak pulse current capability: 40A ($t_p = 8/20\mu$ s) per IEC 61000-4-5 ±2kV ($t_p = 1.2/50\mu$ s, $R_s = 42\Omega$) per IEC 61000-4-5 for unsymmetrical lines
- High EFT Withstand Voltage: ±4kV (100kHz and 5kHz, 5/50ns) IEC 61000-4-4
- Constant clamping voltage across the rated peak
 pulse current range and temperature range
- Protects one I/O or power line
- Working voltage:14V
- Solid-state technology

Mechanical Characteristics

- Package: DFN 1.6mm x 1.6mm x 0.55mm 6-Lead
- Pb-Free, Halogen Free, RoHS/WEEE Compliant
- Molding compound flammability rating: UL 94V-0
- Lead Finish: Lead-Free
- Marking: Marking code and Date Code
- Packaging: Tape and Reel

Applications

- 12V Power Line Protection
- Panels & Displays
- Industrial Equipment
- Solid-State Drives
- Remote Meters
- IoT Devices

Functional Diagram



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Absolute Maximum Rating (T=25°C unless otherwise specified)

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20 \mu s$)	P _{PK}	792	W
Peak Pulse Current ($t_p = 8/20\mu s$)	I _{PP}	40	А
ESD per IEC 61000-4-2 (Air) ⁽¹⁾ ESD per IEC 61000-4-2 (Contact) ⁽¹⁾	V _{ESD}	±30 ±30	kV
Operating Temperature	T _{OP}	-55 to +125	°C
Junction & Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Electrical Characteristics (T=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	V _{RWM}	Pin 4, Pin 5 and Pin 6 to Pin 1, Pin 2 and Pin 3			14	V
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA, Pin 4, Pin 5 and Pin 6 to Pin 1, Pin 2 and Pin 3	17	18.3	19	V
Forward Voltage	V _F	$I_t = 1$ mA, Pin 1, Pin 2 and Pin 3 to Pin 4, Pin 5 and Pin 6		0.5		V
Reverse Leakage Current	I _R	$V_{RWM} = 14V$, Pin 4, Pin 5 and Pin 6 to Pin 1, Pin 2 and Pin 3		86	600	nA
Clamping Voltage ⁽²⁾	V _c	I _{pp} =24A, t _p = 1.2/50μs (Voltage), 8/20μs (Current) Combination Wave- form, R _s =2Ω, Pin 4, Pin 5 and Pin 6 to Pin 1, Pin 2 and Pin 3		18.8	19.8	v
		I _{pp} =40A, t _p = 1.2/50μs (Voltage), 8/20μs (Current) Combination Wave- form, R _s =2Ω, Pin 4, Pin 5 and Pin 6 to Pin 1, Pin 2 and Pin 3		18.8	19.8	V
Dynamic Resistance ^{(2), (3)}	R _{DYN}	t _p = 8/20μs		20		mΩ
Junction Capacitance	C	$V_{R} = 14V, f = 1MHz$		145		pF

Notes:

1) ESD gun return path connected to ESD ground plane.

2) Parameter guaranteed by design.

3) Dynamic resistance measured between 1A and 40A ($t_p = 8/20\mu s$).

Typical Characteristics

Clamping Voltage ($t_p = 1.2/50 \mu s$, $I_{pp} = 24A$)



Clamping Voltage vs. Peak Pulse Current ($t_p=8x20\mu s$)



Peak Pulse Current (t_p=8x20µs) vs Temperature



Clamping Voltage (t_p=1.2/50µs, l_{pp}= 40A)



Clamping Voltage ($t_p=1.2/50\mu s$, at I_{pp}) vs Temperature







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Typical Characteristics

Capacitance vs. Temperature





Capacitance vs. Reverse Voltage

Dynamic Leakage vs. Signal Slew Rate over Temperature

8

Voltage (V)

10

12

14

16

6

100

0

0

T_A = 25°C f = 1 MHz

2

4



Reverse Leakage vs. Temperature



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Application Information

Description

Transient Diverting Suppressors(TDS) are designed to provide high energy EOS protection with superior clamping and temperature characteristics when compared to standard TVS devices.

Conventional pn-junction TVS diodes have an inherent, fixed resistance value or dynamic resistance (R_{DYN}). TVS clamping voltage is given by the equation: $V_{c} = V_{BR} + I_{PP} * R_{DYN}$. Since the dynamic resistance is a fixed value, clamping voltage increases with increased I_{PP} resulting in a linear rise in clamping over the peak pulse current range. Additionally, conventional TVS dissipate surge energy in the junction of the device. Therefore, the capability to absorb transient current is related to the junction area and junction (ambient) temperature. As ambient temperature increases, the clamping voltage increases and the maximum I_{PP} capability decreases.

Transient Diverting Suppressors use a surge rated FET as the main protection element (Figure 1). The FET behaves like a voltage controlled switch which is activated by a precision trigger circuit (Figure 2). During an EOS event, transient voltage increases beyond the breakdown voltage of the trigger circuit. This in turn activates the drive circuit and turns on the shunt FET, effectively "closing the switch" and conducting transient current to ground. As the I_{PP} rises, the FET Rds(on) decreases to a negligibly small value, resulting in a clamping voltage with the same approximate value as the trigger circuit breakdown voltage. Therefore, the TDS clamping voltage is nearly constant across the rated peak pulse current range. The clamping also remains stable over the operating temperature range.

Trigger Circuit Gnd

Figure 1- Functional Diagram





Application Information

Pin Configuration

TDS1411P is in a 1.6 x 1.6mm, 6-pin DFN package. The input or connection to the protected bus is made at pins 4, 5, and 6. Ground connection is made at pins 1, 2, and 3. All pins must be connected for maximum peak pulse current handling capability.





Layout Guidelines

Figure 7 shows a recommended layout for TDS1411P. All the I/O pins (Pin 4, 5 and 6) are connected through a single straight trace. All of the I/O pins must be connected for maximum surge performance. Likewise, all GND pins (Pin 1, 2 and 3) must be connected for maximum surge current capability. If ground is on a different layer of the PCB, connection with multiple vias is recommended. This aids in reducing the parasitic inductance to ground. Note that under transient conditions, the energy is dissipated in the device and no "thermal pad" is needed.

TDS1411P should be located as close to the connector as possible. This aids in restricting transient coupling to adjacent traces, especially during fast rise time ESD events.



Vias to Ground Plane

Figure 7 - PCB Layout Recommendation

Outline Drawing - DFN 1.6mm x 1.6mm x 0.55mm 6-Lead



Land Pattern - DFN 1.6mm x 1.6mm x 0.55mm 6-Lead

Revision Date

11/2/2023



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Marking Code



Notes: 1. XX: Date Code.

2. Dot indicates Pin 1 location.

Tape and Reel Specification



Ordering Information

Part Number	Qty per Reel	Reel Size
TDS1411P.C	3,000	7″



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